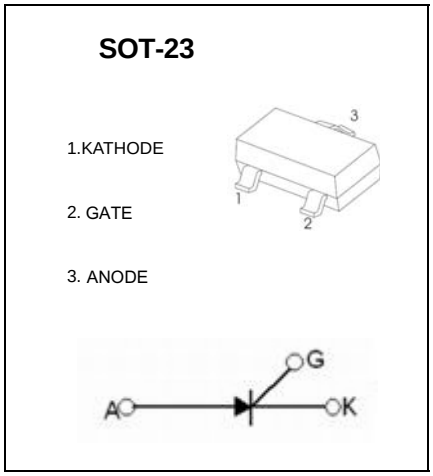
# Plastic-Encapsulate Thyristors

## Silicon Controlled Rectifier




### FEATURES

- Current-$I_{GT}$: 200 μA
- $I_{TRMS}$: 0.8 A
- $V_{RRM}$/ $V_{DRM}$: MCR100-6: 400 V
  MCR100-8: 600 V
- Operating and storage junction temperature range
  $T_J$, $T_{stg}$: -55℃ to +150℃

### ELECTRICAL CHARACTERISTICS（Ta=25℃ unless otherwise specified）

| Parameter | Symbol | | Test conditions | Min | Max | Unit |
|---|---|---|---|---|---|---|
| **On state voltage** | $V_{TM}$* | | $I_{TM}$=1A | | 1.7 | V |
| **Gate trigger voltage** | $V_{GT}$ | | $V_{AK}$=7V | | 0.8 | V |
| **Peak Repetitive forward and reverse blocking voltage**<br>**MCR100-6**<br>**MCR100-8** | $V_{DRM}$ AND $V_{RRM}$ | | $I_{DRM}$= 10 μA | 400<br>600 | | V |
| **Peak forward or reverse blocking Current** | $I_{DRM}$<br>$I_{RRM}$ | | $V_{AK}$= Rated $V_{DRM}$ or $V_{RRM}$ | | 10 | μA |
| **Holding current** | $I_H$ | | $I_{HL}$= 20mA ,$V_{AK}$ = 7V | | 5 | mA |
| **Gate trigger current** | $I_{GT}$ | A2 | $V_{AK}$=7V | 5 | 15 | μA |
| | | A1 | | 15 | 30 | μA |
| | | A | | 30 | 80 | μA |
| | | B | | 80 | 200 | μA |

* Forward current applied for 1 ms maximum duration，duty cycle≤1%。

## Typical Characteristics